



JMTP170N06A

Description

JMT N-channel Enhancement Mode Power MOSFET

Features

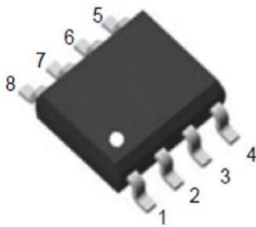
- 60V, 10A
 $R_{DS(ON)} < 15.9m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 21.2m\Omega @ V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free

Application

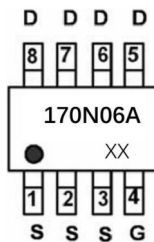
- Load Switch
- PWM Application
- Power Management



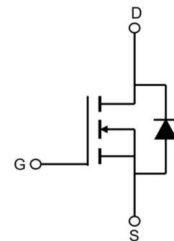
100% UIS TESTED!



SOP-8



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel (pcs)	Per Carton (pcs)
170N06A	JMTP170N06A	TAPING	SOP-8	13"	4000	48000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	10
		$T_A = 100^\circ C$	6.5
I_{DM}	Pulsed Drain Current ^{note1}	40	A
EAS	Single Pulsed Avalanche Energy ^{note2}	64	mJ
P_D	Power Dissipation	$T_A = 25^\circ C$	1.64
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	76	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} = 0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.7	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =10V, I _D =10A	-	12.7	15.9	mΩ
		V _{GS} =4.5V, I _D =5A	-	16.3	21.2	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	2030	-	pF
C _{oss}	Output Capacitance		-	130	-	pF
C _{rss}	Reverse Transfer Capacitance		-	115	-	pF
Q _g	Total Gate Charge	V _{DD} =30V, I _D =5A, V _{GS} =10V	-	46	-	nC
Q _{gs}	Gate-Source Charge		-	7	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	10	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =5A, R _{GEN} =1.8Ω, V _{GS} =10V	-	9	-	ns
t _r	Turn-on Rise Time		-	15	-	ns
t _{d(off)}	Turn-off Delay Time		-	36	-	ns
t _f	Turn-off Fall Time		-	6	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	10	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	40	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =10A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F =10A, dI/dt=100A/μs	-	16	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	13	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : Starting T_J=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=16A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

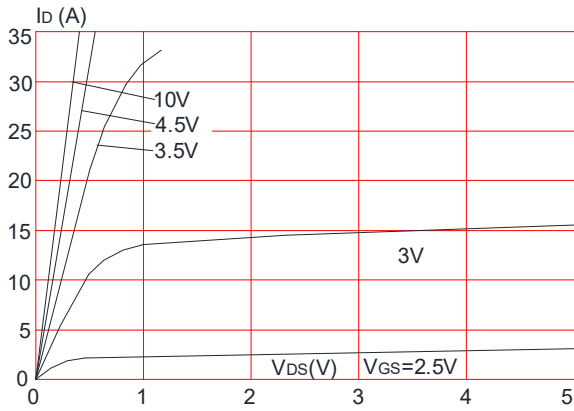


Figure 2: Typical Transfer Characteristics

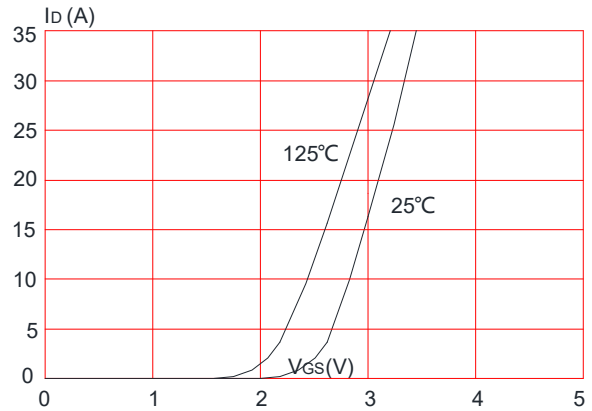


Figure 3: On-resistance vs. Drain Current

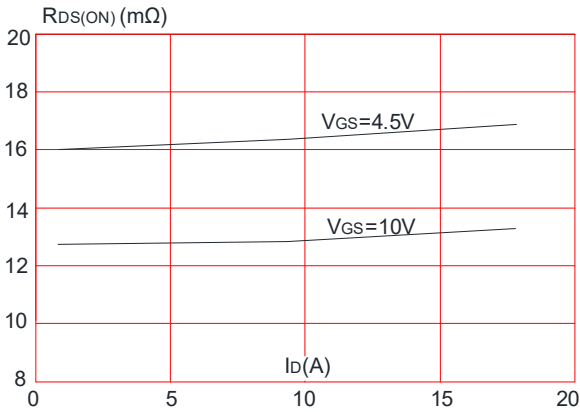


Figure 4: Body Diode Characteristics

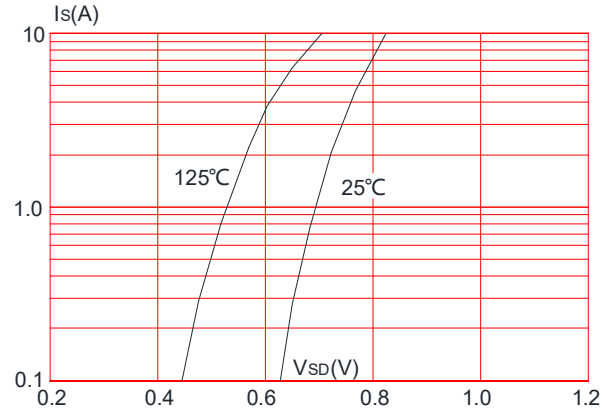


Figure 5: Gate Charge Characteristics

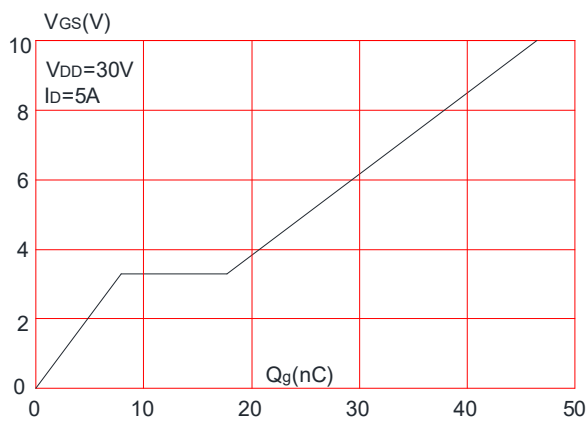


Figure 6: Capacitance Characteristics

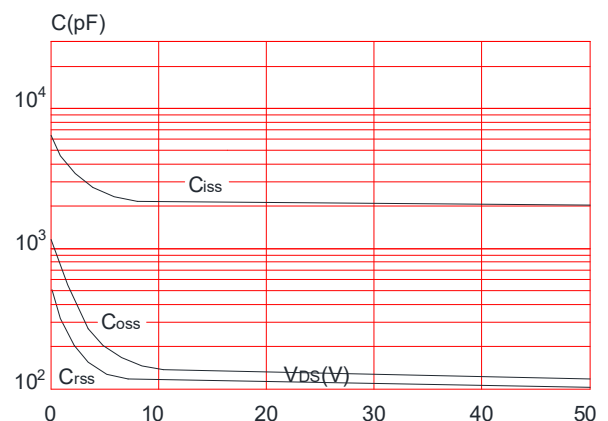




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

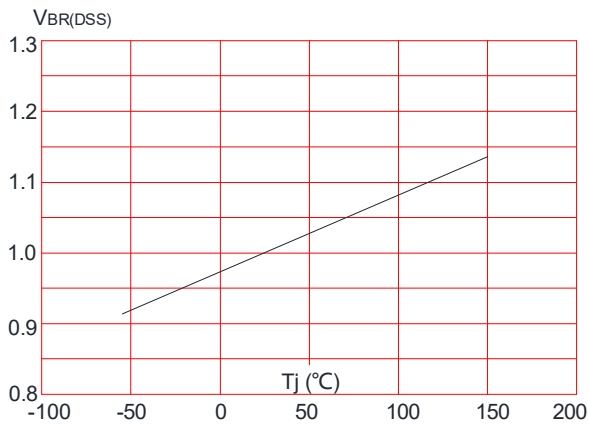


Figure 8: Normalized on Resistance vs. Junction Temperature

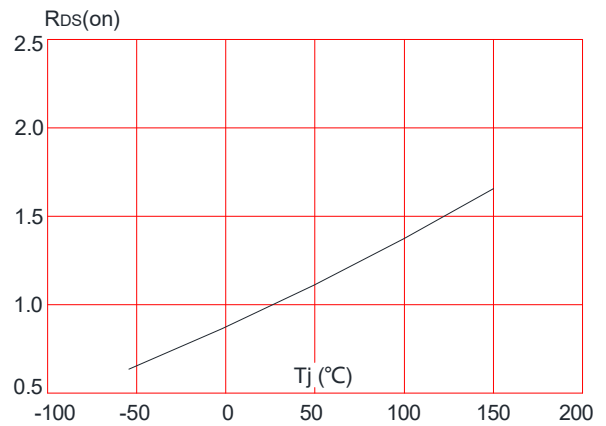


Figure 9: Maximum Safe Operating Area

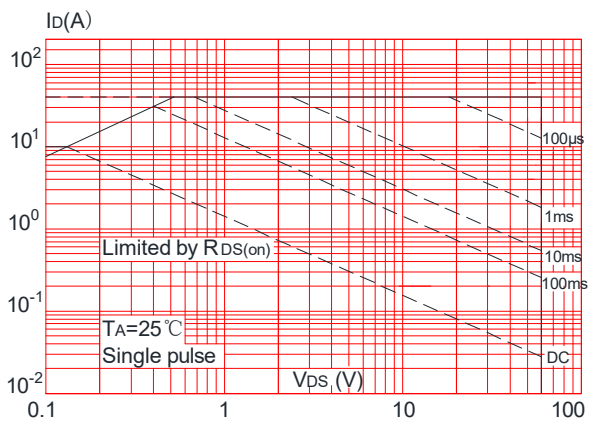


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

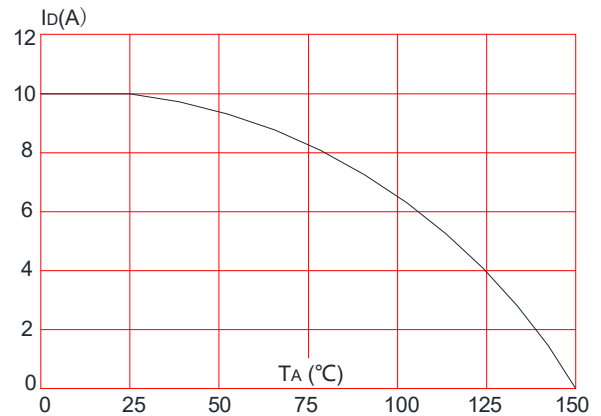
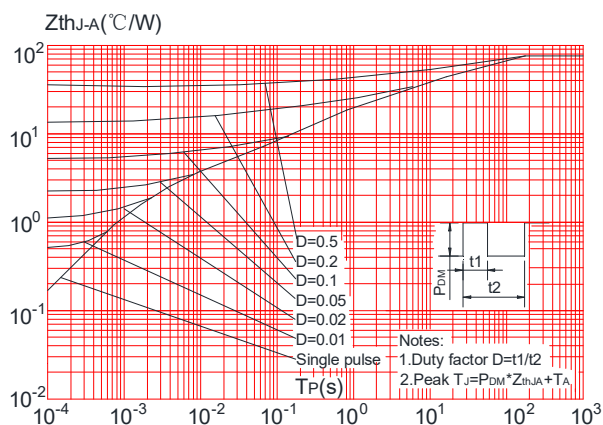


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit



Figure1:Gate Charge Test Circuit & Waveform

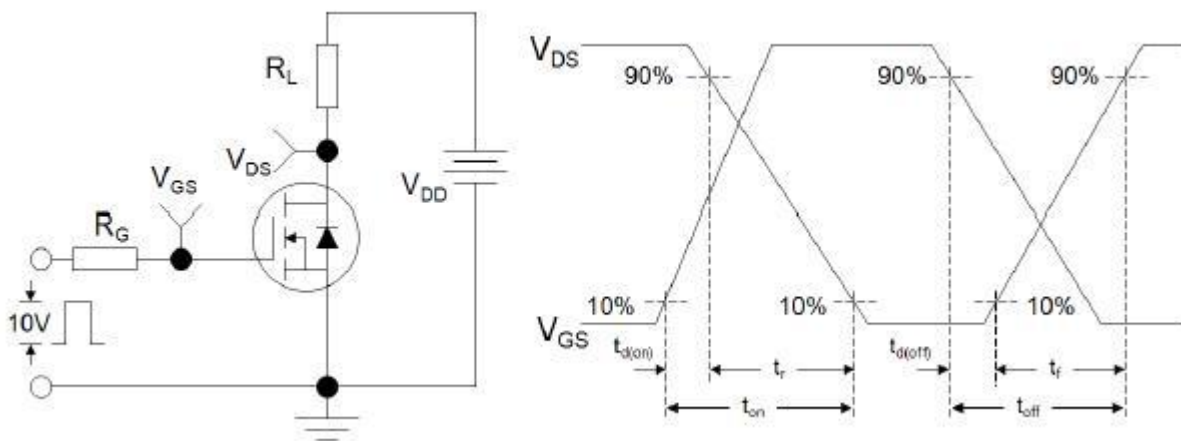


Figure 2: Resistive Switching Test Circuit & Waveforms

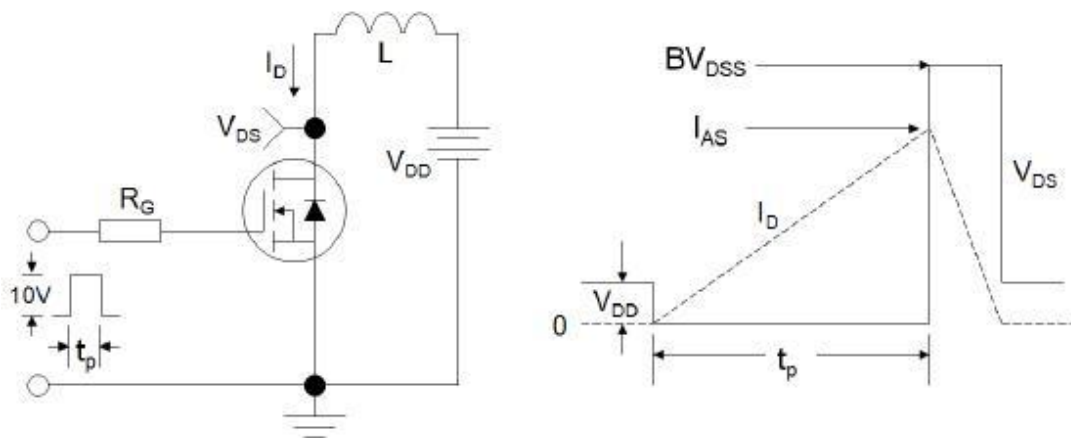
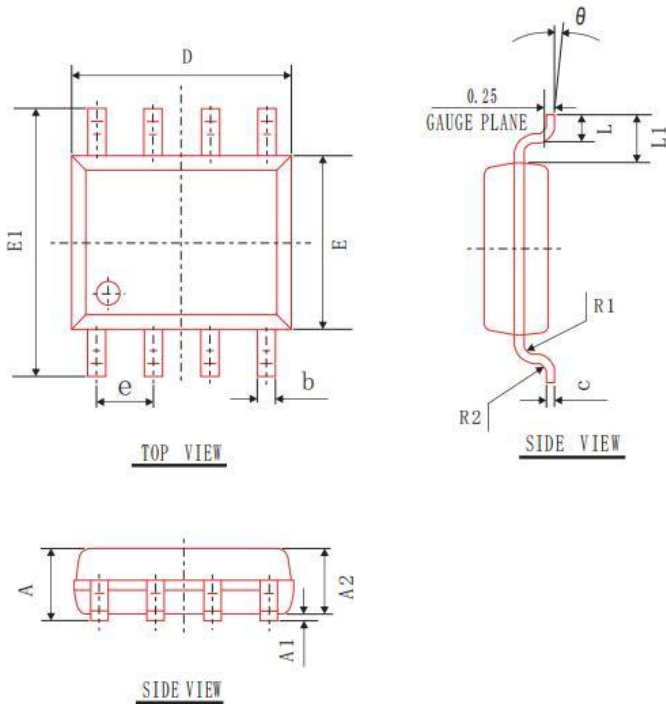


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Package Mechanical Data-SOP-8

COMMON DIMENSIONS
(UNITS OF MEASURE=mm)



SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L 1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		

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